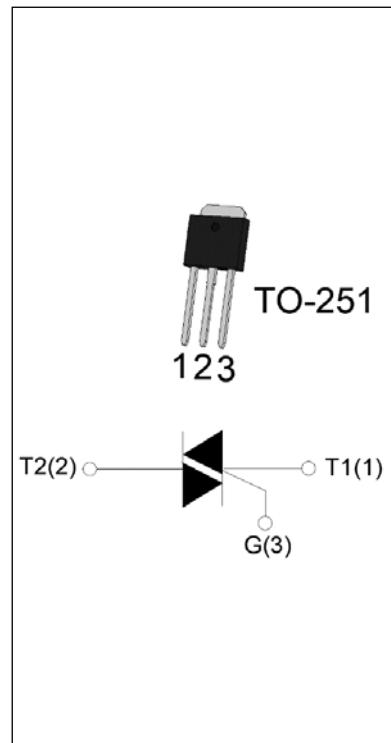


**DESCRIPTION:**

The JST08H-600TW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST08H-600TW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\text{ I/II/III}}$	5/5/5	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c \leqslant 91^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	dI/dt	50	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage (T _j =25°C; non-repetitive,off-state;FIG.7)	V _{PP}	1.5	kV
--	-----------------	-----	----

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	I - II -III	MAX.	5	mA
V _{GT}		I - II -III	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ		MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III	MAX.	10	mA
		II		15	
I _H	I _T =100mA		MAX.	10	mA
dV/dt	V _D =400V Gate Open T _j =125°C		MIN.	150	V/μs
(dI/dt)c	(dV/dt)c=10V/μs, T _j =125°C		MIN.	0.5	A/ms
t _{on}	I _G =10mA I _A =200mA I _R =20mA T _j =25°C	TYP.	2	μs	
t _{off}			20		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =11A	t _p =380μs	1.5	V
V _{TO}	Threshold voltage	T _j =125°C	0.8	V
R _D	Dynamic resistance	T _j =125°C	44	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	5	μA
I _{RRM}		T _j =125°C	0.25	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	3	°C/W
R _{th(j-a)}	junction to ambient (AC)	120	°C/W

ORDERING INFORMATION

<u>J</u>	<u>ST</u>	<u>08</u>	<u>H</u>	<u>-600</u>	<u>TW</u>
JieJie Microelectronics Co., Ltd.					
	Triacs				
		IT(RMS):8A			
			H:TO-251		
				TW:IGT1-3≤5mA	
				600:VDRM /VRRM≥600V	

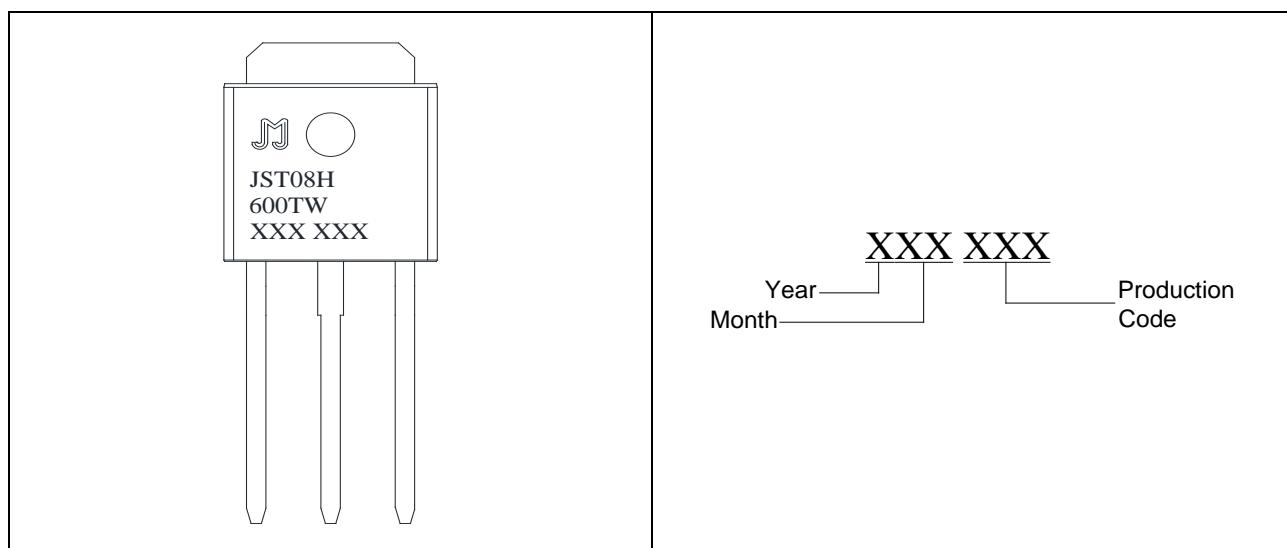
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

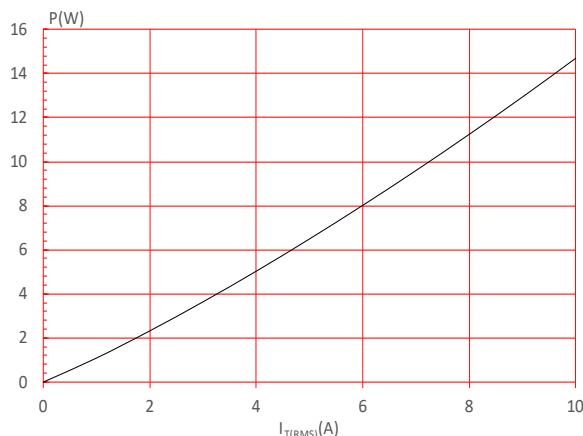


FIG.3: Surge peak on-state current versus number of cycles

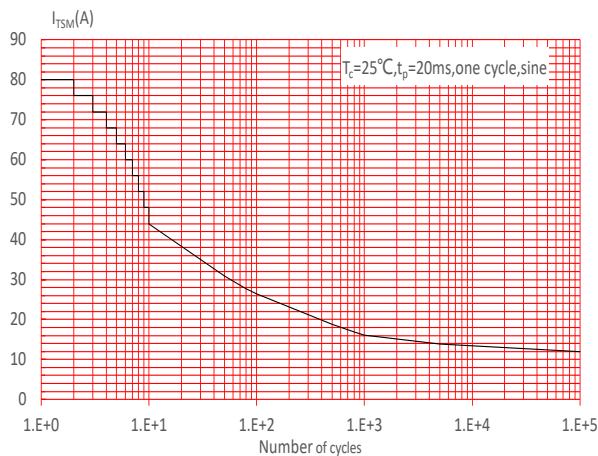


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($\text{d}I/\text{d}t < 50\text{A}/\mu\text{s}$)

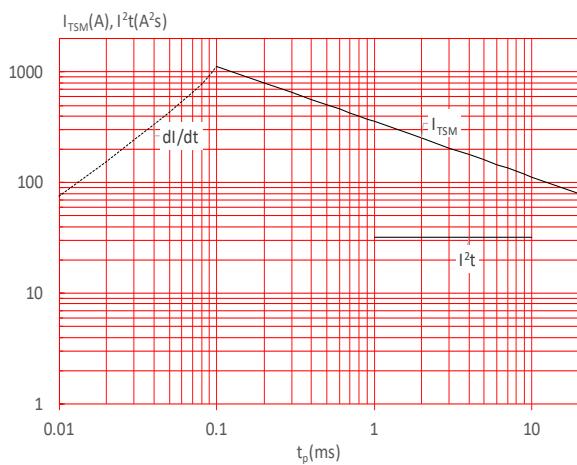


FIG.2: RMS on-state current versus case temperature

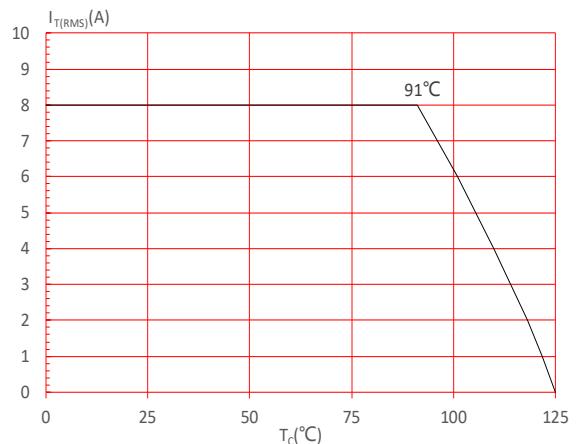


FIG.4: On-state characteristics

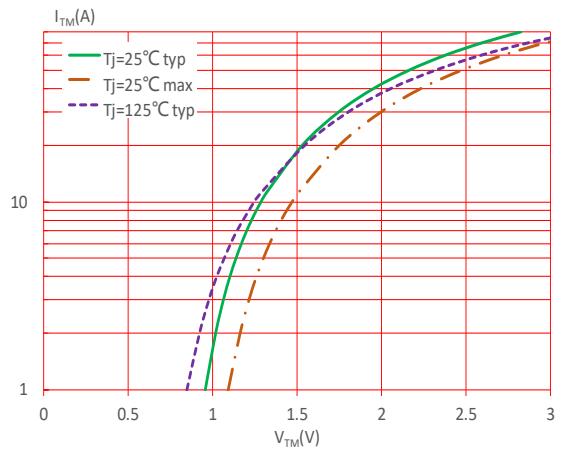


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

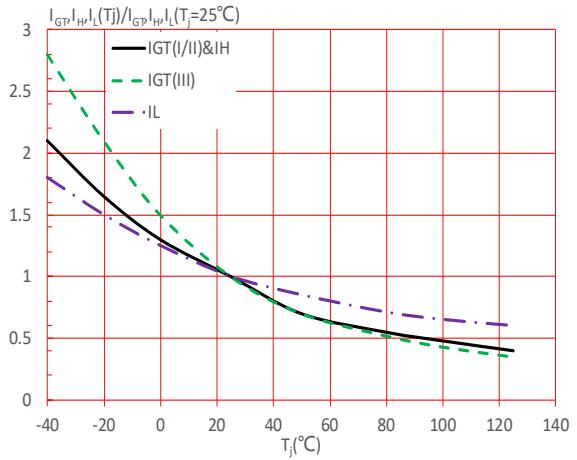
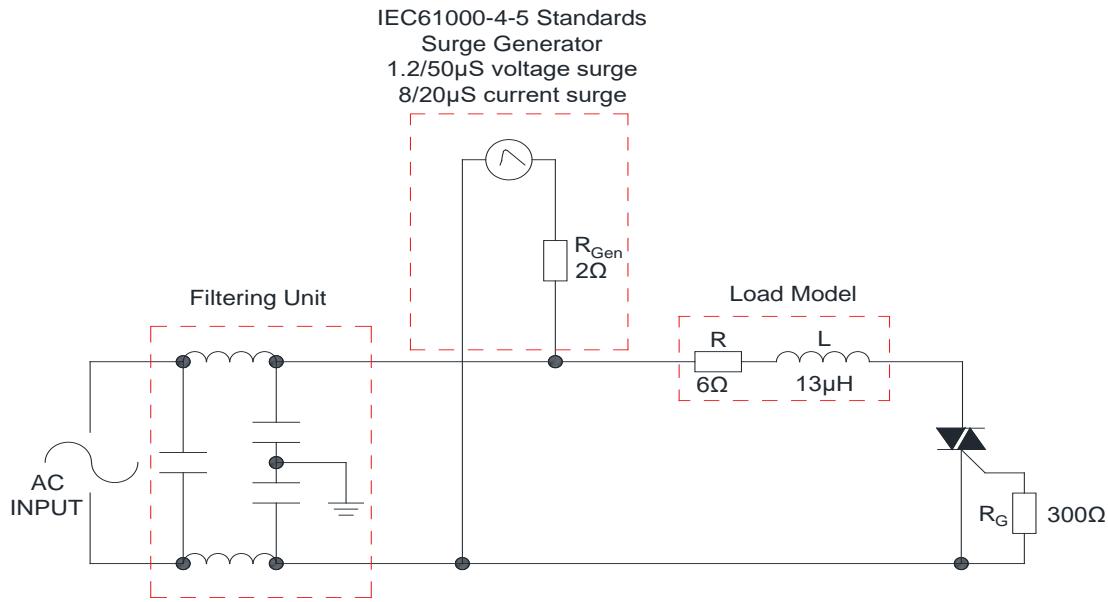


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

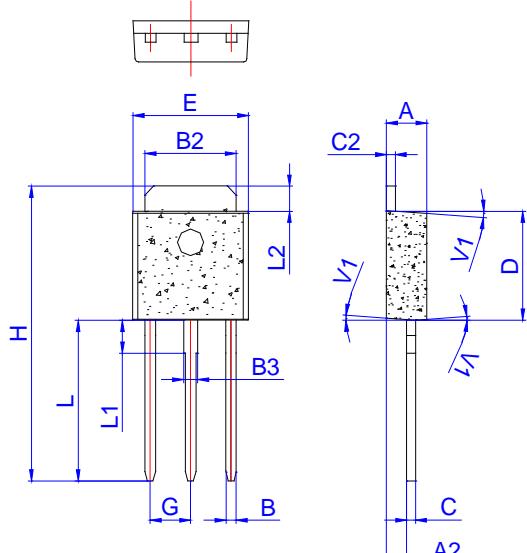
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST08H-600TW	600	5	TO-251	80	Tube

Document Revision History

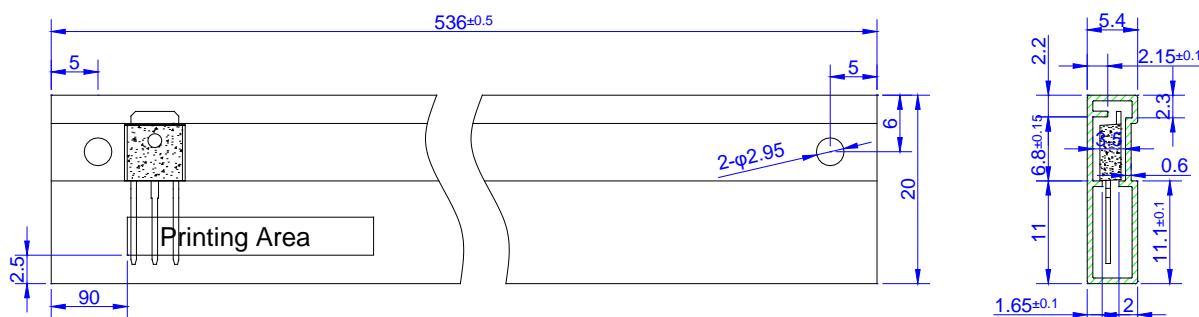
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1		4°			4°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000

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